

MOSFETs Silicon N-Channel MOS (DTMOSVI)

TK190U65Z

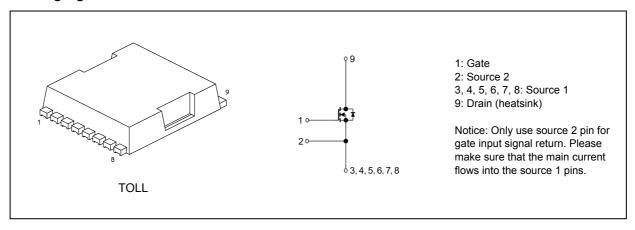
1. Applications

· Switching Power Supplies

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 0.149 \Omega$ (typ.)
- (2) High-speed switching properties with the lower capacitance.
- (3) Enhancement mode: $V_{th} = 3$ to $4 \text{ V} (V_{DS} = 10 \text{ V}, I_D = 0.61 \text{ mA})$

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

Characteristics			Symbol	Rating	Unit
Drain-source voltage			V _{DSS}	650	V
Gate-source voltage			V _{GSS}	±30	
Drain current (DC)		(Note 1)	I _D	15	Α
Drain current (pulsed)		(Note 1)	I _{DP}	60	
Power dissipation	(T _c = 25 °C)		P _D	130	W
Single-pulse avalanche energy		(Note 2)	E _{AS}	165	mJ
Single-pulse avalanche current			I _{AS}	3.7	Α
Reverse drain current (DC)		(Note 1)	I _{DR}	15	
Reverse drain current (pulsed)		(Note 1)	I _{DRP}	60	
Channel temperature			T _{ch}	150	℃
Storage temperature		_	T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production



5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	0.961	°C/W

Note 1: Ensure that the channel temperature does not exceed 150 $^{\circ}\text{C}.$

Note 2: V_{DD} = 90 V, T_{ch} = 25 °C (initial), L = 21.4 mH, I_{AS} = 3.7 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

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6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±1	μА
Drain cut-off current	I _{DSS}	V _{DS} = 650 V, V _{GS} = 0 V	_	_	2	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	650	_	_	V
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 0.61 mA	3	_	4	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 7.5 A	_	0.149	0.19	Ω

6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 300 V, V _{GS} = 0 V, f = 100 kHz	_	1370	_	pF
Reverse transfer capacitance	C _{rss}		_	1.5	_	
Output capacitance	C _{oss}		_	34	_	
Effective output capacitance	C _{o(er)}	V _{DS} = 0 to 400 V, V _{GS} = 0 V	_	53	_	
Gate resistance	r _g	V _{DS} = OPEN , f = 1 MHz	_	3	_	Ω
Switching time (rise time)	t _r	See Figure 6.2.1	_	14	_	ns
Switching time (turn-on time)	t _{on}		_	34	_	
Switching time (fall time)	t _f		_	4	_	
Switching time (turn-off time)	t _{off}		_	66	_	
MOSFET dv/dt ruggedness	dv/dt	$V_{DS} \le V_{(BR)DSS}, I_D \le 7.5 A$	70	_	_	V/ns

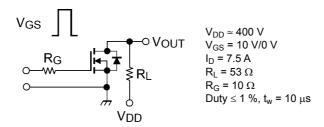


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 15 \text{ A}$	_	25		nC
Gate-source charge 1	Q _{gs1}		_	7.9	_	
Gate-drain charge	Q _{gd}		_	7.1	_	

6.4. Source-Drain Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V_{DSF}	I _{DR} = 15 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time		V _{DD} = 400 V,	_	270	_	ns
Reverse recovery charge	Q_{rr}	I _{DR} = 7.5 A, V _{GS} = 0 V -dI _{DR} /dt = 100 A/μs	_	3.0	_	μС
Peak reverse recovery current	I _{rr}	-αι _{DR} /αι – 100 Α/μ3	_	22	_	Α
Diode dv/dt ruggedness	dv/dt	$V_{DD} \le 400 \text{ V}, I_{DR} \le 7.5 \text{ A}, V_{GS} = 0 \text{ V}$	40	_	_	V/ns



7. Marking (Note)

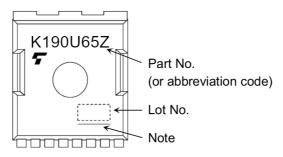


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.



8. Characteristics Curves (Note)

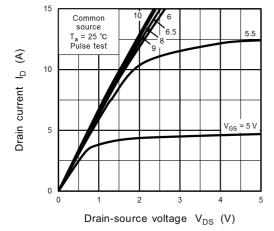


Fig. 8.1 I_D - V_{DS}

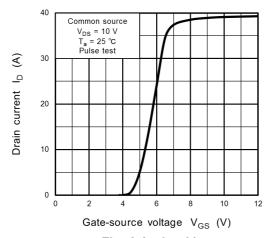


Fig. 8.3 ID - VGS

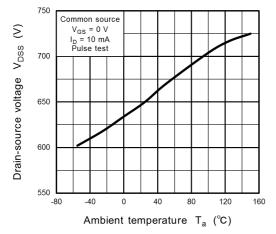


Fig. 8.5 V_{DSS} - T_a

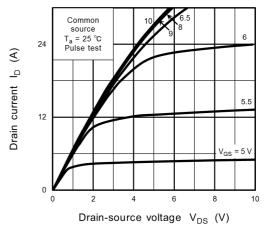


Fig. 8.2 I_D - V_{DS}

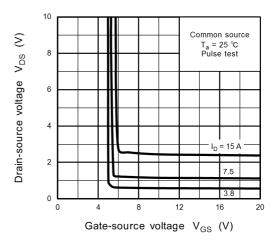


Fig. 8.4 VDS - VGS

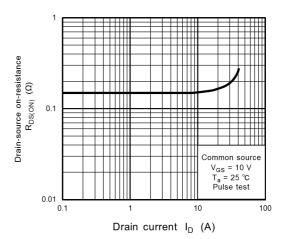
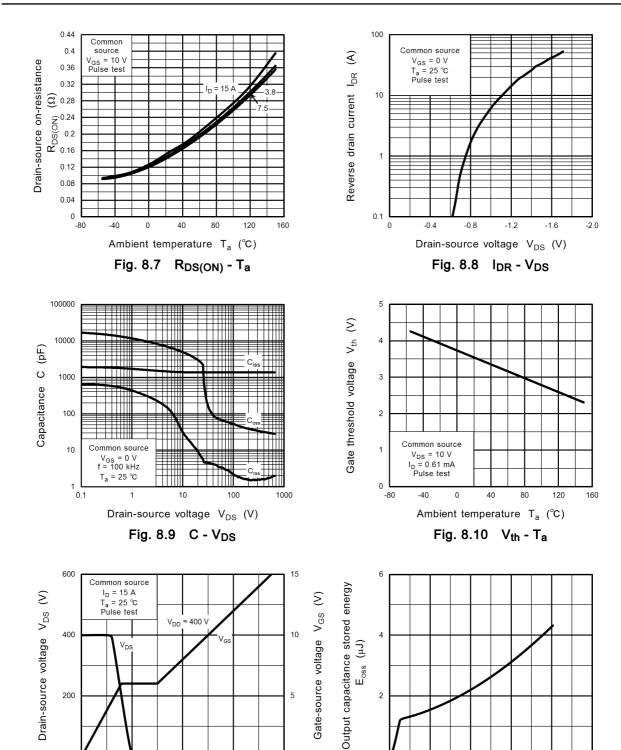


Fig. 8.6 R_{DS(ON)} - I_D





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Drain-source voltage V_{DS} (V) Fig. 8.12 Eoss - V_{DS}

0

0

40



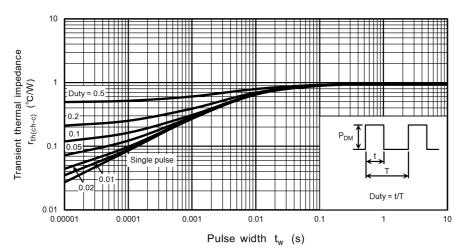
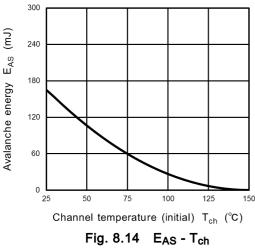


Fig. 8.13 rth - tw (Guaranteed Maximum)



(Guaranteed Maximum)

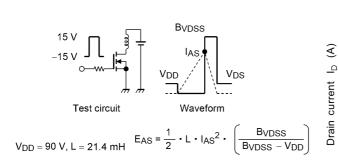


Fig. 8.16 Test Circuit/Waveform

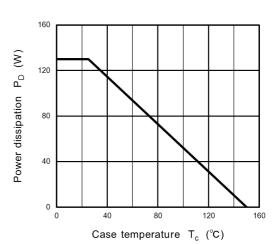


Fig. 8.15 P_D - T_c (Guaranteed Maximum)

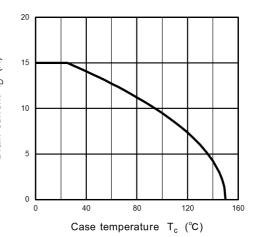


Fig. 8.17 I_D - T_c (Guaranteed Maximum)



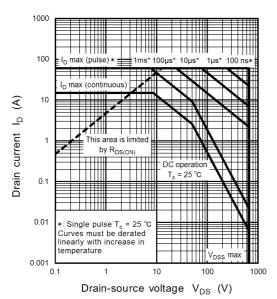


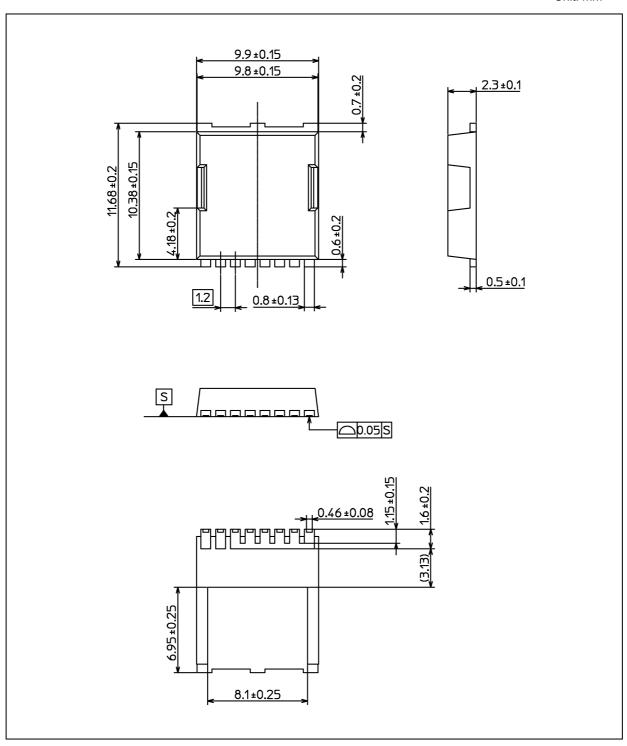
Fig. 8.18 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.75 g (typ.)

Package Name(s)
TOSHIBA: 2-10AF1A
Nickname: TOLL



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